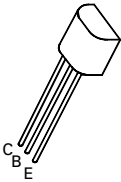


PNP SILICON PLANAR SMALL SIGNAL TRANSISTOR

ISSUE 2 – MARCH 94

ZTX541



E-Line
TO92 Compatible

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-100	V
Collector-Emitter Voltage	V_{CEO}	-100	V
Emitter-Base Voltage	V_{EBO}	-5	V
Continuous Collector Current	I_C	-100	mA
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	300	mW
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +175	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-100			V	$I_C = -100\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-100			V	$I_C = -10\mu A$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	$I_E = -100\mu A$
Collector Cut-Off Current	I_{CBO}			-0.5	μA	$V_{CB} = -80V$
Emitter Cut-Off Current	I_{CER}			-0.5 -10	μA μA	$V_{CE} = -80V, R_{BE} = 50K\Omega$ $V_{CE} = -80V, R_{BE} = 50K\Omega$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.5	V	$I_C = -2mA, I_B = -0.1mA$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			-1.0	V	$I_C = -2mA, I_B = -0.1mA$
Static Forward Current Transfer Ratio	h_{FE}	30				$I_C = -2mA, V_{CE} = -1V$
Transition Frequency	f_T	80			MHz	$I_C = -5mA, V_{CE} = -5V$ $f = 60MHz$
Output Capacitance	C_{obo}			10	pF	$V_{CB} = -6V, f = 1MHz$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$

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TYPICAL CHARACTERISTICS

